



General Description

The WSF80P04 is the highest performance trench P-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate chargefor most of the synchronous buck converterapplications.

The WSF80P04 meet the RoHS and GreenProduct requirement 100% EAS guaranteed withfull function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

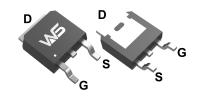
Product Summery

BV _{DSS}	R _{DSON}	I _D
-40V	7mΩ	-80A

Applications

- Motor Drivers.
- Primary Switch for 12V Systems.
- Load Switch.

TO-252 Pin Configuration





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Symbol	Parameter	Units	
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ -10V ¹	-80	Α
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ -10V ¹	-38	Α
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ -10V ¹	-13	А
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ -10V ¹	-10	Α
I _{DM}	Pulsed Drain Current ^{2,} T _C =25°C	-210	Α
EAS	Avalanche Energy, Single pulse,L=0.1mH	1008	mJ
I _{AS}	Avalanche Current, Single pulse,L=0.1mH	-142	Α
P _D @T _C =25℃	Total Power Dissipation ⁴	78	W
P _D @T _C =100°C	Total Power Dissipation ⁴	37	W
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$
T_J	Operating Junction Temperature Range -55 to 150		

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		1.8	°C/W



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40			V	
D	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _{DS} =-27		7	10	mΩ	
R _{DS(ON)}		V _{GS} =-4.5V, I _{DS} =-17A		9	14	mΩ	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.3	-1.8	-2.3	V	
		V _{DS} =-32V , V _{GS} =0V , T _J =25°C			-1	- uA	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V , V _{GS} =0V , T _J =85℃			-30		
I _{GSS}	Gate-Source Leakage Current	$V_{\text{GS}} = \pm 25 \text{V}$, $V_{\text{DS}} = 0 \text{V}$			±100	nA	
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.5		Ω	
Qg	Total Gate Charge (10V)			51	71		
Q_gs	Gate-Source Charge	V_{DS} =-20V , V_{GS} =-4.5V , I_{D} =-27A		9		nC	
Q _{gd}	Gate-Drain Charge			11			
T _{d(on)}	Turn-On Delay Time			11	20		
T _r	Rise Time	V_{DD} =-20V, R_L =20 Ω , I_{DS} =-1A,		14	25		
T _{d(off)}	Turn-Off Delay Time	V_{GEN} =-10V, R_G =6 Ω		41	74	ns	
T _f	Fall Time			77	139		
C _{iss}	Input Capacitance			5500	5857		
C _{oss}	Output Capacitance	V _{DS} =-20V , V _{GS} =0V , f=1MHz		560	660 pF		
C _{rss}	Reverse Transfer Capacitance			500			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			-80	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-13A , T _J =25℃		-0.8	-1.1	V
t _{rr}	Reverse Recovery Time	I- 004 II/II 4004/ . T 05°C		28		nS
Q_{rr}	Reverse Recovery Charge	IF=20A,dI/dt=100A/μs,T _J =25℃		20		nC

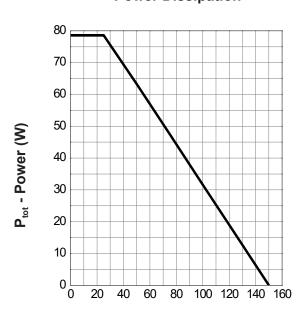
Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec. 2. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DS} =-20V, V_{GS} =-10V,L=0.1mH,I_{AS}=-142A
- 4. The power dissipation is limited by 150 $^{\circ}$ C junction temperature 5. The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



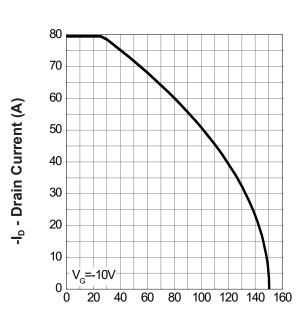
Typical Characteristics

Power Dissipation



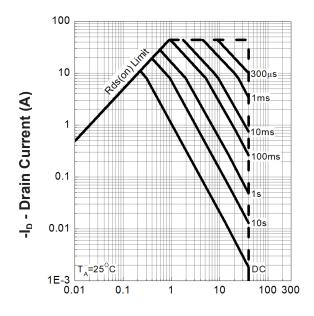
T_c - Case Temperature (°C)

Drain Current



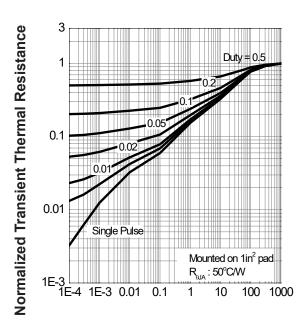
T_c - Case Temperature (°C)

Safe Operation Area



-V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance

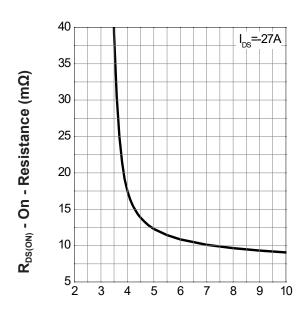


Square Wave Pulse Duration (sec)



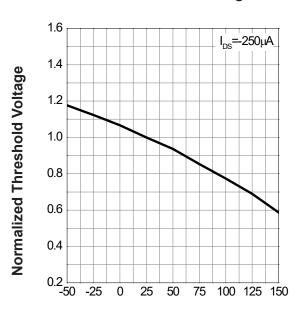
Typical Characteristics (Cont.)

Gate-Source On Resistance



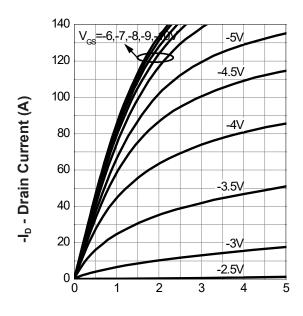
-V_{GS} - Gate - Source Voltage (V)

Gate Threshold Voltage



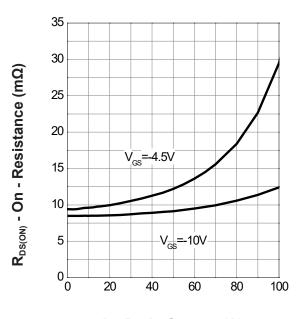
T_i - Junction Temperature (°C)

Output Characteristics



 $-V_{DS}$ - Drain - Source Voltage (V)

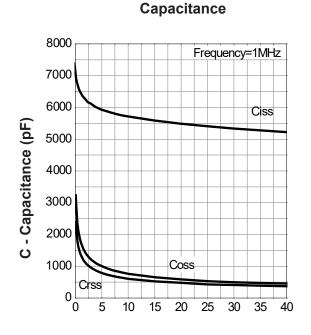
Drain-Source On Resistance



-I_D - Drain Current (A)

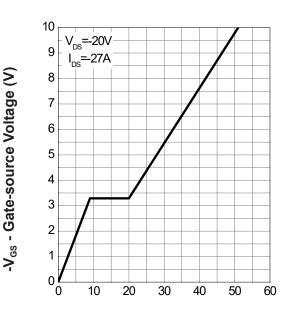


Typical Characteristics (Cont.)



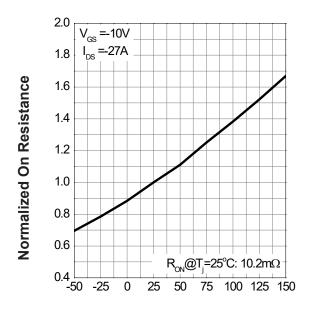
-V_{DS} - Drain-Source Voltage (V)

Gate Charge



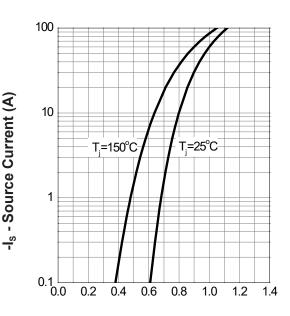
Q_G - Gate Charge (nC)

Drain-Source On Resistance



T_j - Junction Temperature (°C)

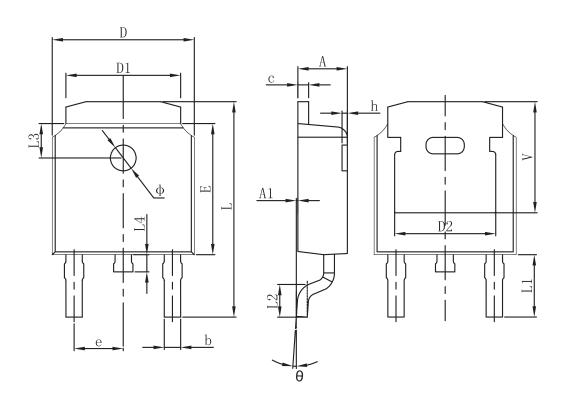
Source-Drain Diode Forward



-V_{SD} - Source - Drain Voltage (V)



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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